# STGP10NC60KD-VB Datasheet

## 600V Trench and Fieldstop IGBT

| PRODUCT SUMMARY | | |
|---|---|---|
| $V_{CE}$ (V) | 600 | |
| $I_C$ (A) | 20 (TC=25°C) | 10(TC=100°C) |
| $V_{CE}$ (sat) (V) | 1.7 | |
| $I_{CM}$ (A) | 30 | |

### FEATURES

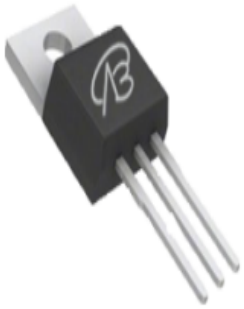
- Very Low VCEsat
- Low turn-off losses
- High speed switching
- Maximum junction temperature 175°C
- Ultra low gate charge ($Q_g$)
- Avalanche energy rated (UIS)

RoHS COMPLIANT
HALOGEN FREE

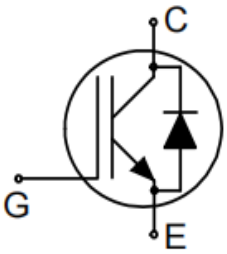
### APPLICATIONS

- Telecommunications
  - Server and telecom power supplies
- Lighting
  - High-intensity discharge (HID)
  - Fluorescent ballast lighting
- Consumer and computing
  - ATX power supplies
- Industrial
  - Welding
  - Battery chargers
- Renewable energy
  - Solar (PV inverters)
- Switch mode power supplies (SMPS)

TO-220



Top View




### Package pin definition

- Pin1 G - Gate
- Pin2 C & backside - Collector
- Pin3 E - Emitter

**ABSOLUTE MAXIMUM RATINGS** ($T_C$ = 25 °C, unless otherwise noted)

| PARAMETER | | | SYMBOL | LIMIT | UNIT |
|---|---|---|---|---|---|
| Collector-Emitter Voltage | | | $V_{CE}$ | 600 | V |
| Gate-Emitter Voltage | | | $V_{GE}$ | ±30 | |
| Continuous Collector Current ($T_J$ = 150 °C) | $V_{GE}$ at 15 V | $T_C$ = 25 °C | $I_C$ | 20 | A |
| | | $T_C$ = 100 °C | | 10 | |
| Pulsed Collector Current [a] | | | $I_{CM}$ | 30 | |
| Diode Forward Current [b] | | | $I_F$ | 10 | A |
| Maximum Power Dissipation | | $T_C$ = 25 °C | $P_D$ | 150 | W |
| | | $T_C$ = 100 °C | | 62 | W |
| Operating Junction and Storage Temperature Range | | | $T_J$, $T_{stg}$ | -55 to +175 | °C |
| Short Circuit Withstand Time TC=150°C | VGE= 15V, VCE≤ 400V | | tsc | 3 | μs |
| Short Circuit Withstand Time TC=100°C | VGE= 15V, VCE≤330V | | | 5 | |
| Soldering Recommendations (Peak Temperature) [c] | for 10 s | | | 260 | °C |

**Notes**

a. Repetitive rating; pulse width limited by maximum junction temperature.

b. Current limited by maximum junction temperature.

c. 1.6 mm from case.

| THERMAL RESISTANCE RATINGS | | | | |
|---|---|---|---|---|
| **PARAMETER** | **SYMBOL** | **TYP.** | **MAX.** | **UNIT** |
| Maximum Junction-to-Ambient | $R_{thJA}$ | - | 78 | °C/W |
| Maximum Junction-to-Case | $R_{thJC}$ | - | 3.6 | |

| **SPECIFICATIONS** ($T_J$ = 25 °C, unless otherwise noted) | | | | | | | |
|---|---|---|---|---|---|---|---|
| **PARAMETER** | **SYMBOL** | **TEST CONDITIONS** | | **MIN.** | **TYP.** | **MAX.** | **UNIT** |
| **Static** | | | | | | | |
| Collector-Emitter Breakdown Voltage | $BV_{CE}$ | $V_{GE}$ = 0 V, $I_C$ = 250 μA | | 600 | - | - | V |
| | | $V_{GE}$ = 0 V, $I_C$ = 1 mA | | 600 | - | - | |
| Gate-Source Threshold Voltage (N) | $V_{GE(th)}$ | $V_{CE}$ = $V_{GE}$, $I_D$ = 250 μA | | 4 | 5 | 6 | V |
| Zero Gate Voltage Collector Current | $I_{CES}$ | $V_{CE}$ = 600 V, $V_{GE}$ = 0 V, $T_J$ = 25 °C | | - | 1 | 20 | μA |
| | | $V_{CE}$ = 600 V, $V_{GE}$ = 0 V, $T_J$ = 150 °C | | - | 1000 | - | μA |
| Gate-Emitter Leakage Current | $I_{GES}$ | $V_{CE}$ = 0 V, $V_{GS}$ = ± 2 0 V | | - | - | 100 | nA |
| Collector-Emitter Saturation Voltage | $V_{CE(sat)}$ | $V_{GE}$ = 15 V | $I_C$ = 10 A | - | 1.7 | 2.1 | V |
| Forward Transconductance | $g_{fs}$ | $V_{CE}$ = 20 V, $I_C$ = 10 A | | - | 18 | - | S |
| **Dynamic** | | | | | | | |
| Input Capacitance | $C_{ies}$ | $V_{GE}$ = 0 V, $V_{CE}$ = 25 V, f = 500 KHz | | - | 1136 | - | pF |
| Output Capacitance | $C_{oes}$ | | | - | 9 1 | - | |
| Reverse Transfer Capacitance | $C_{res}$ | | | - | 32 | - | |
| Turn-on Energy | $E_{on}$ | $V_{CE}$ = 400 V , $V_{GE}$ = 0 /15V, $I_C$ = 10 A, $R_g$ = 10Ω | | - | 0.46 | - | nJ |
| Turn-off Energy | $E_{off}$ | | | - | 0.36 | - | |
| Total Gate Charge | $Q_g$ | $V_{GE}$ = 15 V | $I_C$ = 10 A, $V_{CE}$ = 400 V | - | 8 2 | - | nC |
| Gate-Emitter Charge | $Q_{ge}$ | | | - | 19 | - | |
| Gate to Collector Charge | $Q_{gc}$ | | | - | 25 | - | |
| Turn-On Delay Time | $t_{d(on)}$ | $V_{CE}$ = 400 V , $V_{GE}$ = 0 /15V, $I_C$ = 10 A, $R_g$ = 10Ω | | - | 28 | - | ns |
| Rise Time | $t_r$ | | | - | 42 | - | |
| Turn-Off Delay Time | $t_{d(off)}$ | | | - | 186 | - | |
| Fall Time | $t_f$ | | | - | 34 | - | |
| Internal emitter inductance measured 5 mm | $L_E$ | | | - | 13 | - | nH |
| **Diode Characteristics** | | | | | | | |
| Diode Forward Current | $I_F$ | IGBT symbol showing the integral reverse junction diode | | - | - | 10 | A |
| Pulsed Diode Forward Current | $I_{FM}$ | | | - | - | 30 | |
| Diode Forward Voltage | $V_F$ | $I_F$ = 10 A | | - | 1.65 | 2.0 | V |
| Reverse Recovery Time | $t_{rr}$ | $T_J$ = 25 °C, $I_F$ = 10 A, $dI_F/dt$ = 200 A/μs, $V_R$ = 400 V | | - | 70 | - | ns |
| Reverse Recovery Charge | $Q_{rr}$ | | | - | 0.48 | - | μC |
| Reverse Recovery Current | $I_{RRM}$ | | | - | 8 | - | A |

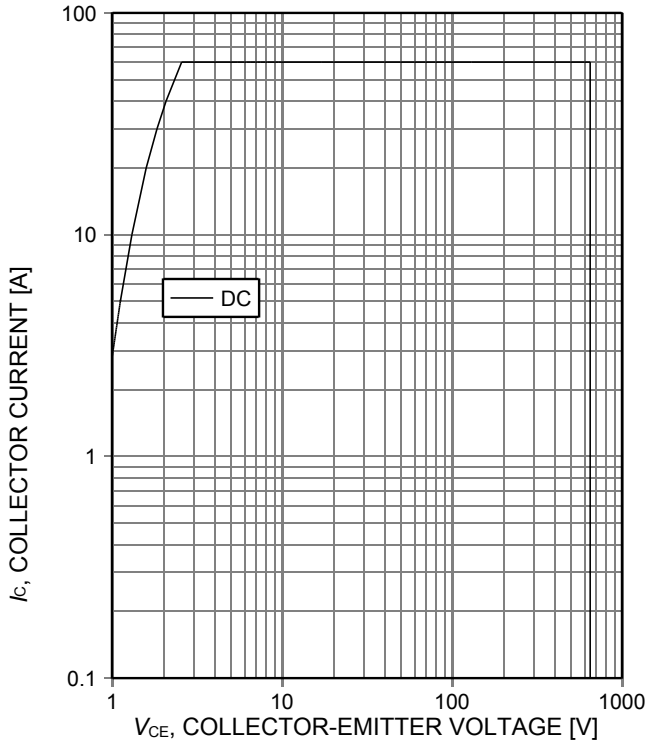



Figure 1. **Forward bias safe operating area** ($D$=0, $T_C$=25°C, $T_{vj}$≤175°C; $V_{GE}$=15V. Recommended use at $V_{GE}$≥7.5V)

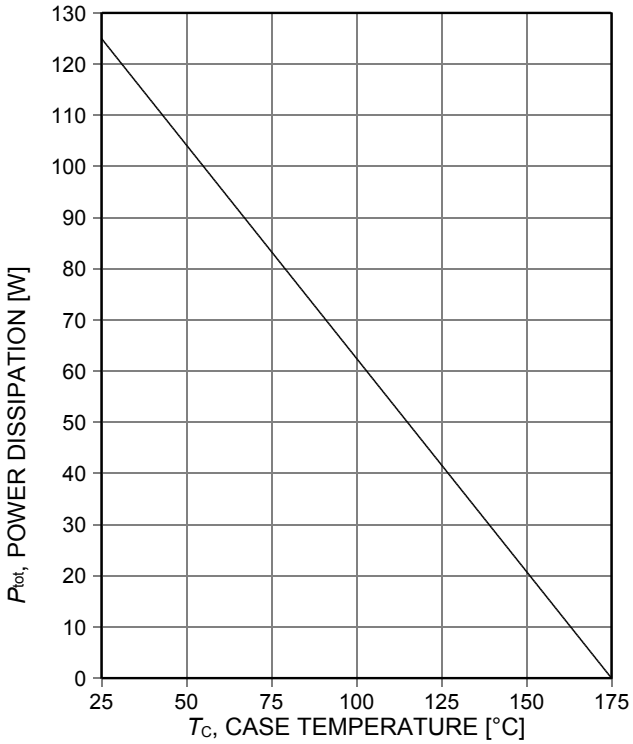



Figure 2. **Power dissipation as a function of case temperature** ($T_{vj}$≤175°C)

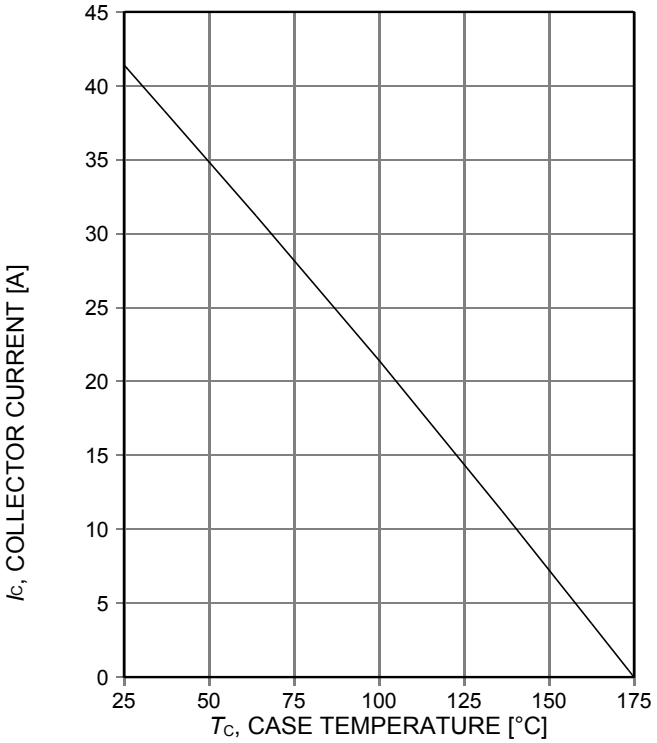



Figure 3. **Collector current as a function of case temperature**

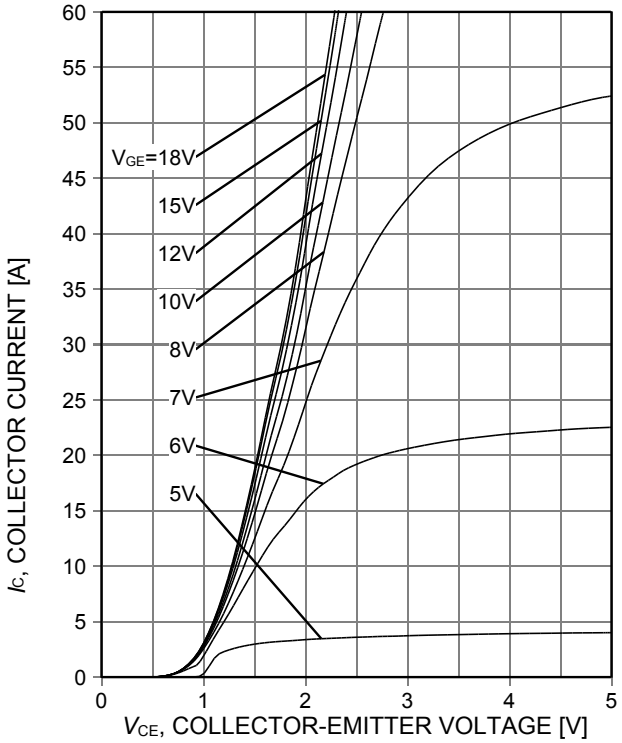



Figure 4. **Typical output characteristic**

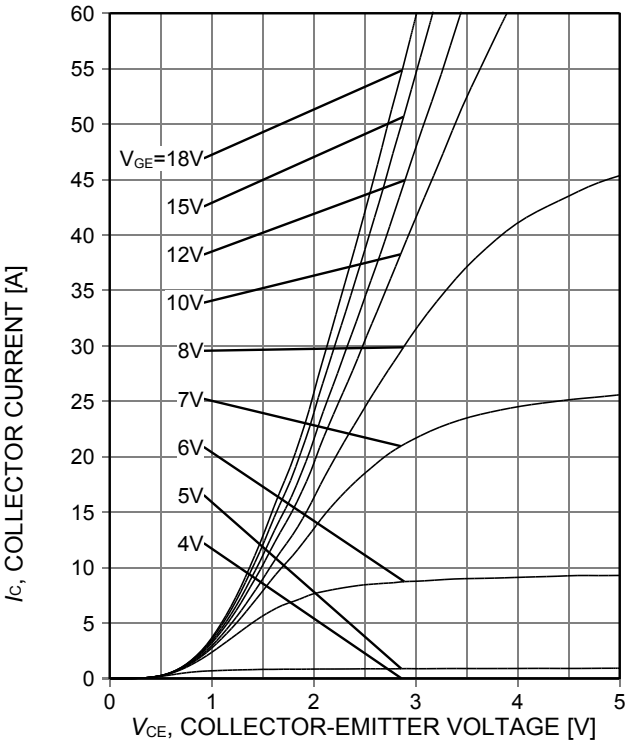



Figure 5. **Typical output characteristic** ($T_{vj}$=150°C)

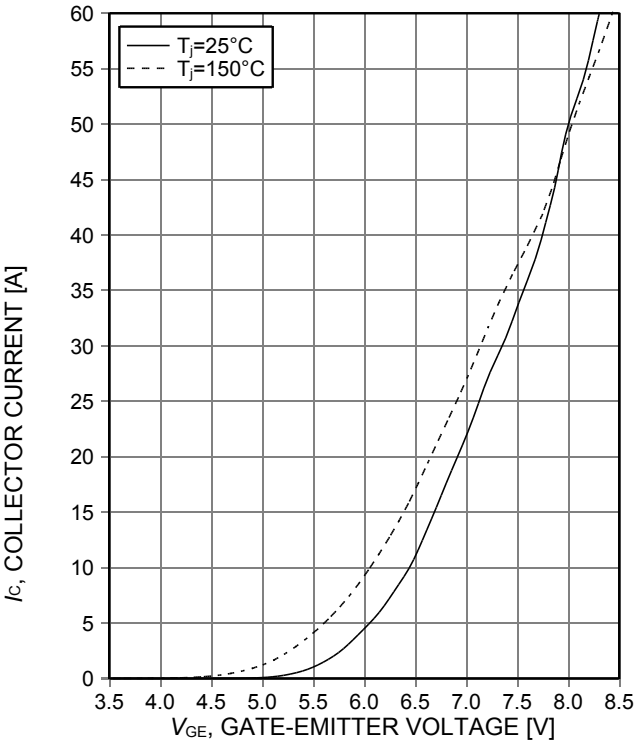



Figure 6. **Typical transfer characteristic** ($V_{CE}$=20V)

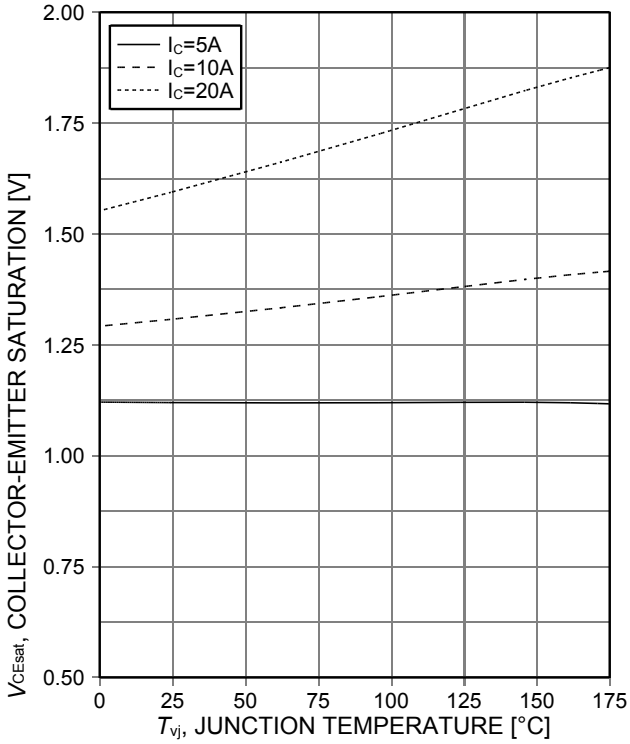



Figure 7. **Typical collector-emitter saturation voltage as a function of junction temperature**

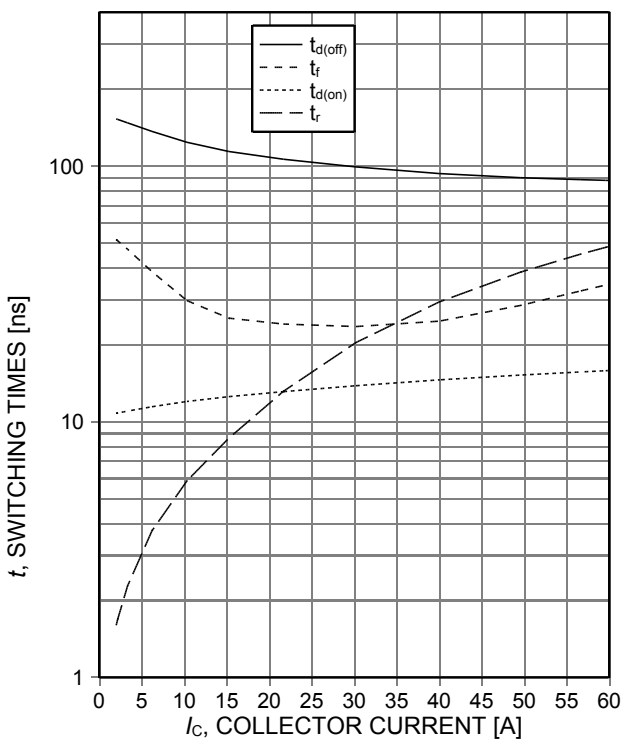



Figure 8. **Typical switching times as a function of collector current**

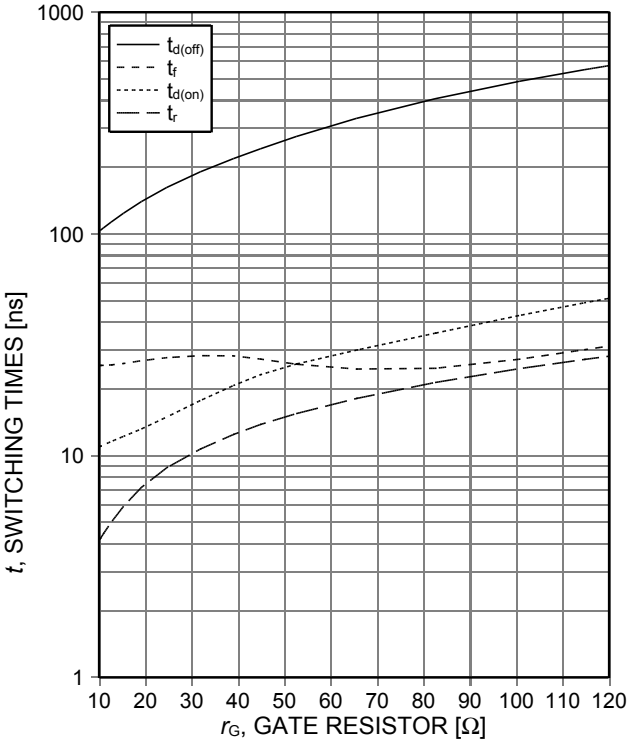



Figure 9. **Typical switching times as a function of gate resistor**

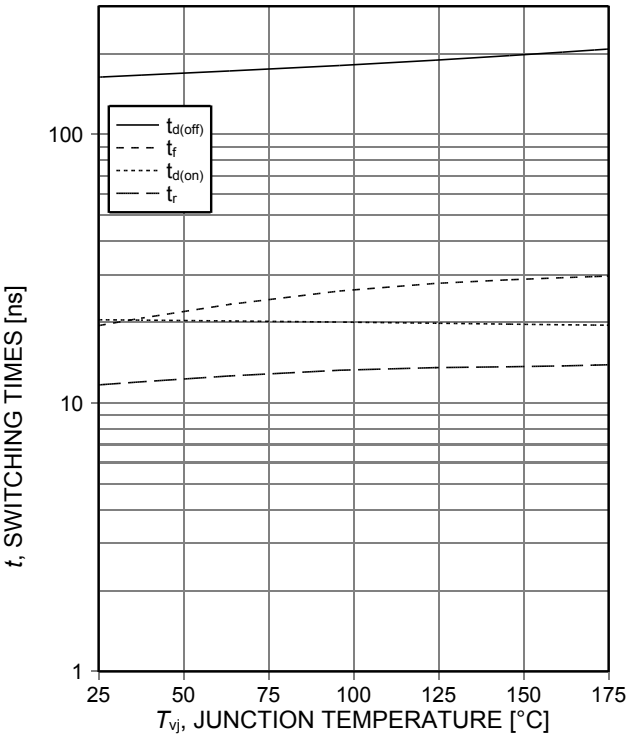



Figure 10. **Typical switching times as a function of junction temperature**

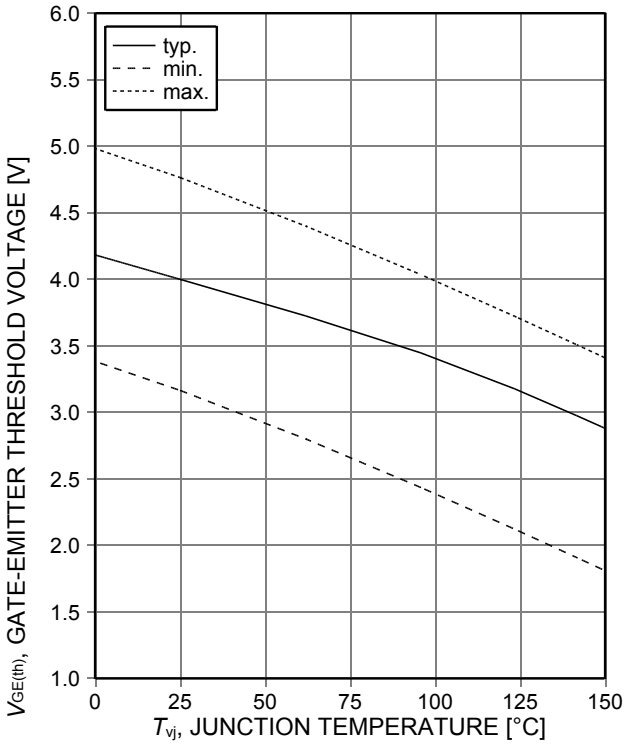



Figure 11. **Gate-emitter threshold voltage as a function of junction temperature**

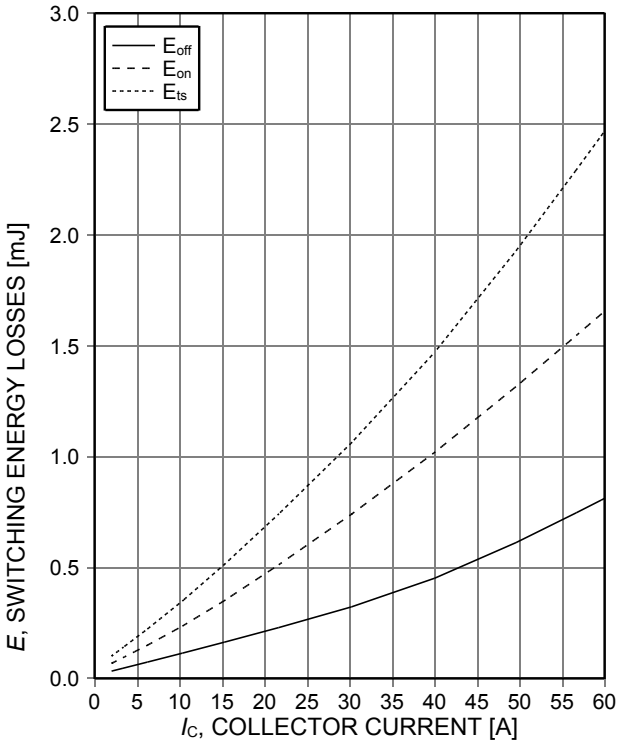



Figure 12. **Typical switching energy losses as a function of collector current**

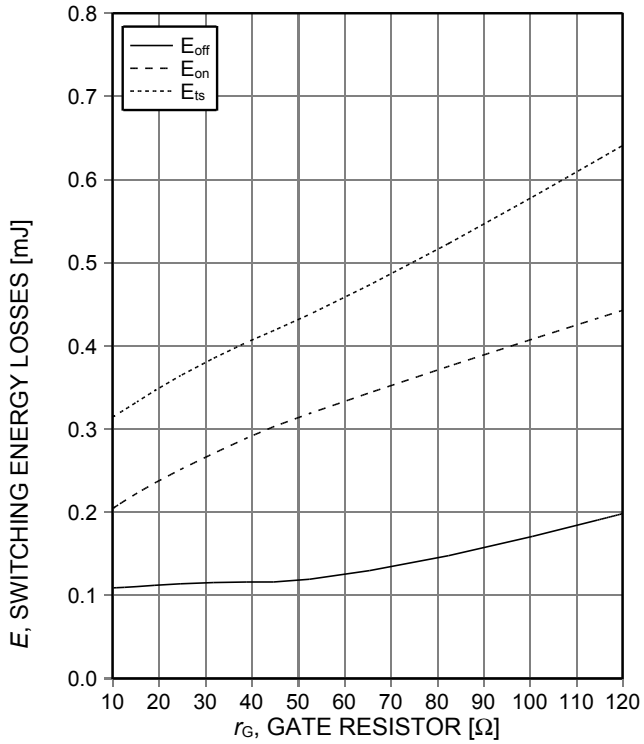



Figure 13. **Typical switching energy losses as a function of gate resistor**

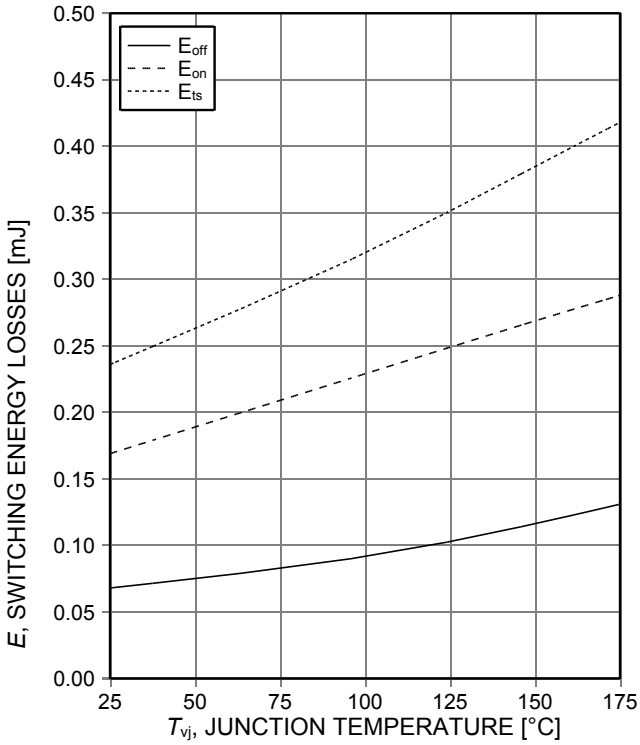



Figure 14. **Typical switching energy losses as a function of junction temperature**

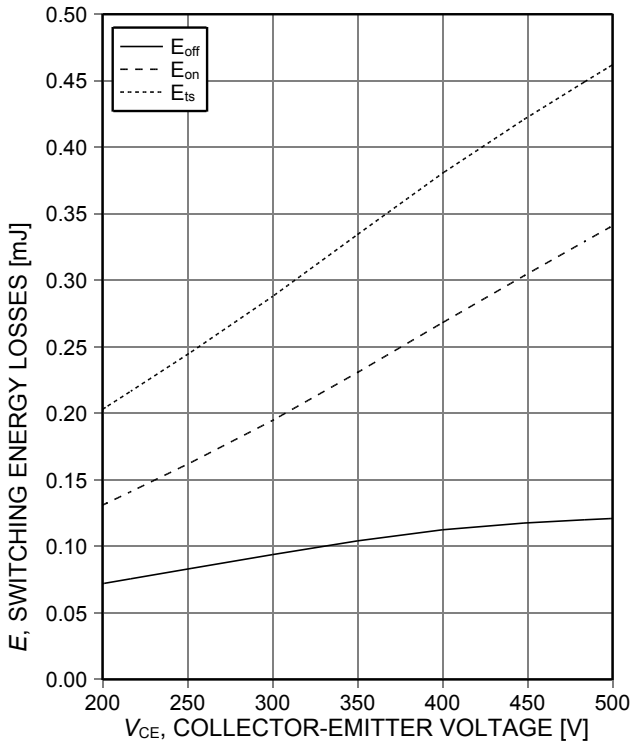



Figure 15. **Typical switching energy losses as a function of collector emitter voltage**

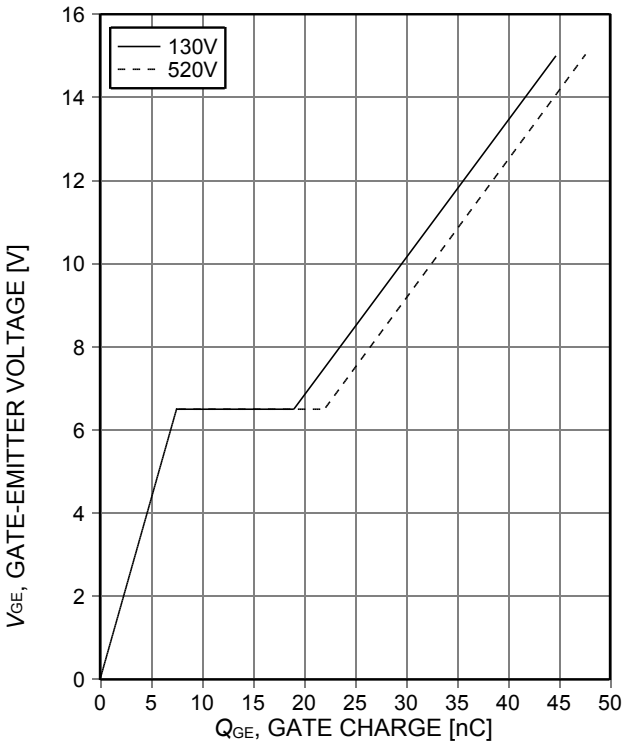



Figure 16. **Typical gate charge**

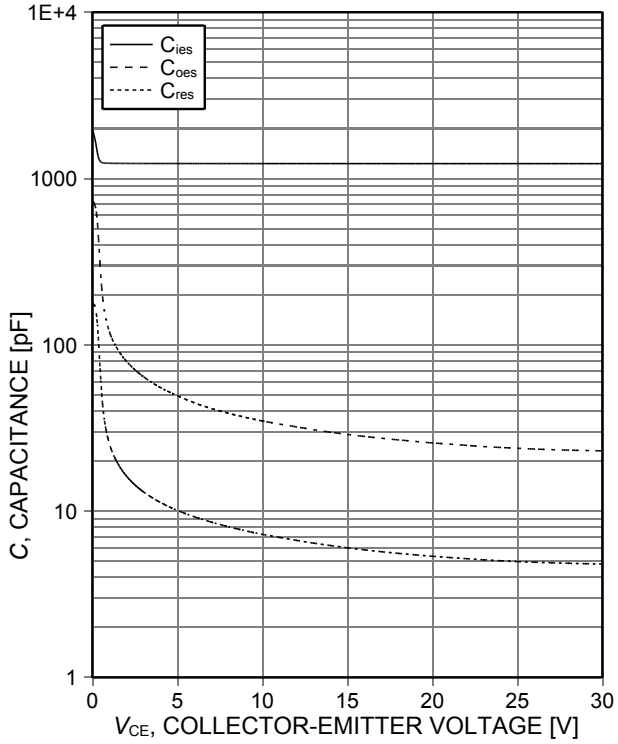



Figure 17. **Typical capacitance as a function of collector-emitter voltage**

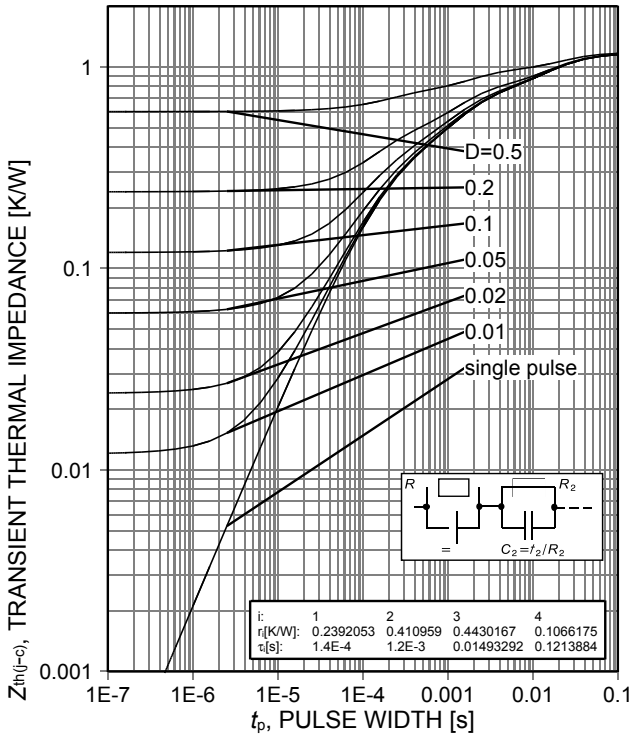



Figure 18. **IGBT transient thermal impedance**

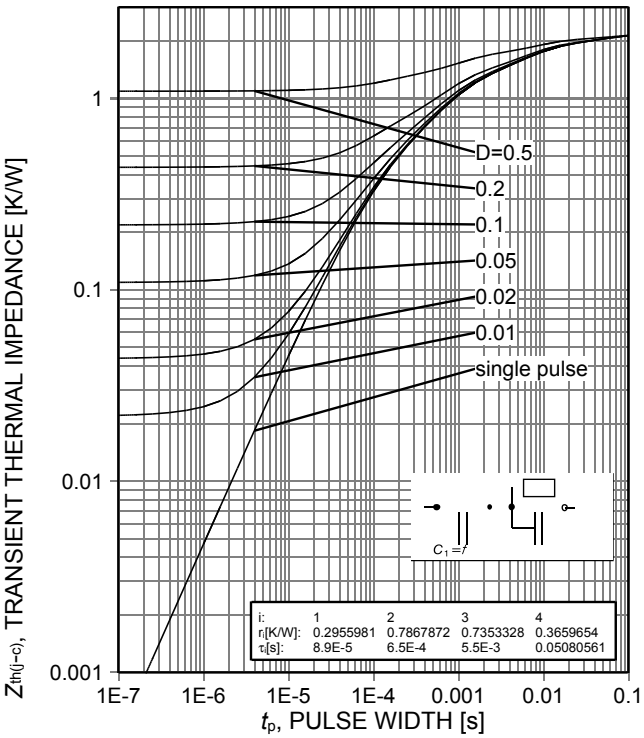



Figure 19. **Diode transient thermal impedance as a function of pulse width**

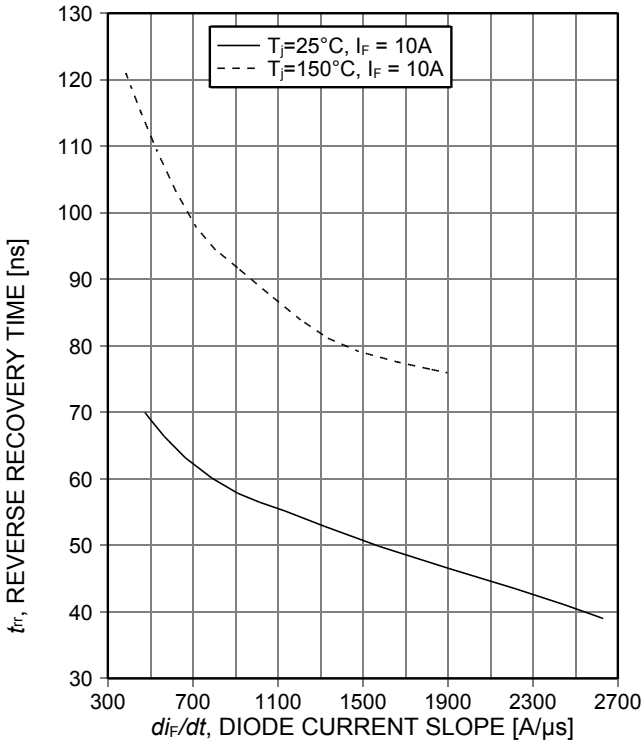
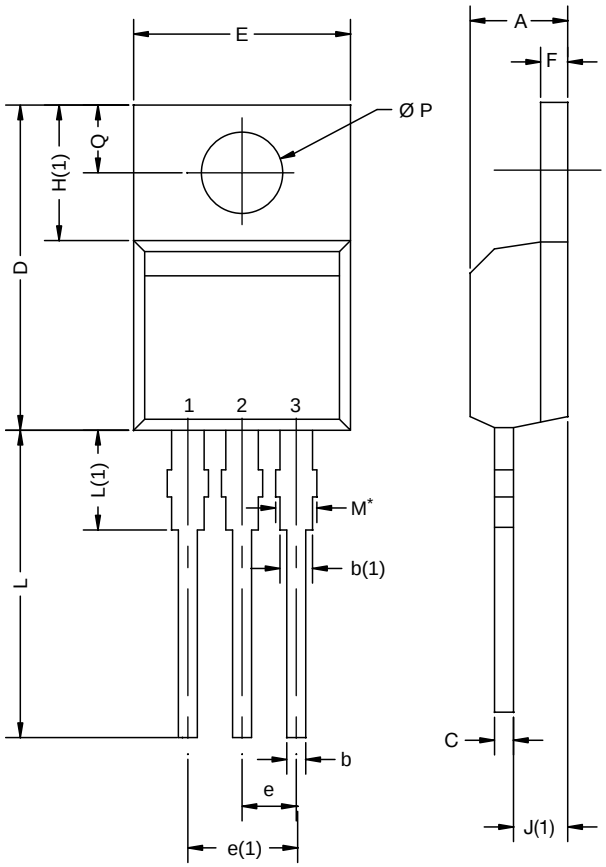



Figure 20. **Typical reverse recovery time as a function of diode current slope**

# TO-220AB




| DIM. | MILLIMETERS | | INCHES | |
|---|---|---|---|---|
| | MIN. | MAX. | MIN. | MAX. |
| A | 4.25 | 4.65 | 0.167 | 0.183 |
| b | 0.69 | 1.01 | 0.027 | 0.040 |
| b(1) | 1.20 | 1.73 | 0.047 | 0.068 |
| c | 0.36 | 0.61 | 0.014 | 0.024 |
| D | 14.85 | 15.49 | 0.585 | 0.610 |
| E | 10.04 | 10.51 | 0.395 | 0.414 |
| e | 2.41 | 2.67 | 0.095 | 0.105 |
| e(1) | 4.88 | 5.28 | 0.192 | 0.208 |
| F | 1.14 | 1.40 | 0.045 | 0.055 |
| H(1) | 6.09 | 6.48 | 0.240 | 0.255 |
| J(1) | 2.41 | 2.92 | 0.095 | 0.115 |
| L | 13.35 | 14.02 | 0.526 | 0.552 |
| L(1) | 3.32 | 3.82 | 0.131 | 0.150 |
| Ø P | 3.54 | 3.94 | 0.139 | 0.155 |
| Q | 2.60 | 3.00 | 0.102 | 0.118 |
| ECN: X12-0208-Rev. N, 08-Oct-12<br>DWG: 5471 | | | | |

**Notes**

* M = 1.32 mm to 1.62 mm (dimension including protrusion) Heatsink hole for HVM

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